# Si-D Consortium Meeting

28.01.2025

Jochen Dingfelder (U. Bonn), Erika Garutti (U. Hamburg)

## Si-D Consortium

### **Si-D Consortium**

#### **WP1: Position-Sensitive Monolithic Detectors**

Dingfelder, Weber

#### WP 1.1

#### CMOS tracking detectors

Bonn, DESY, TU Dortmund, FH Dortmund, Frankfurt, Freiburg, Heidelberg, KIT, Siegen, Göttingen, GSI, HLL-MPG

#### WP 1.2

CMOS detectors for particle identification and energy measurement

HU Berlin, Heidelberg, KIT, DESY

### **WP2: Fast Timing**

Garutti, Galatyuk

#### WP 2.1

#### LGAD sensors

Darmstadt, DESY, Frankfurt, Göttingen, Hamburg, KIT, Mainz, GSI, HLL-MPG, MPP-MPG

WP 2.2

3D sensors

Bonn, DESY, Freiburg, MPP-MPG

#### WP 2.3

CMOS sensors with gain layers

Freiburg, Heidelberg

### **WP3: System Integration and Simulation**

Dierlamm, Karagounis, Masciocchi, Stroth

#### WP 3.1

Power management

Aachen, FH Dortmund

#### WP3.4

Al strips on pCVD diamond carrier

Frankfurt, GSI, Mainz

#### WP3.2

Optical data transmission

Wuppertal, FH Dortmund, KIT

#### WP3.5

Reusability by on-detector intelligence
FH Dortmund

#### WP3.3

2.5D/3D integration

FH Dortmund, KIT, HLL-MPG

WP3.6

Radiation hardness and simulation

Frankurt, GSI, Hamburg, Heidelberg, KIT

### **Cooperation partners**

#### Funded:

Aachen

Bonn

Frankfurt

Freiburg

Göttingen

Hamburg

Heidelberg

**KIT** 

### **Not funded:**

**HU Berlin** 

**TU Darmstadt** 

**FH Dortmund** 

**TU Dortmund** 

Siegen

**Wuppertal** 

### Not on cooperation agreement:

**HU Berlin** 

**TU Darmstadt** 

Wuppertal

### **Associated partners**

Mainz

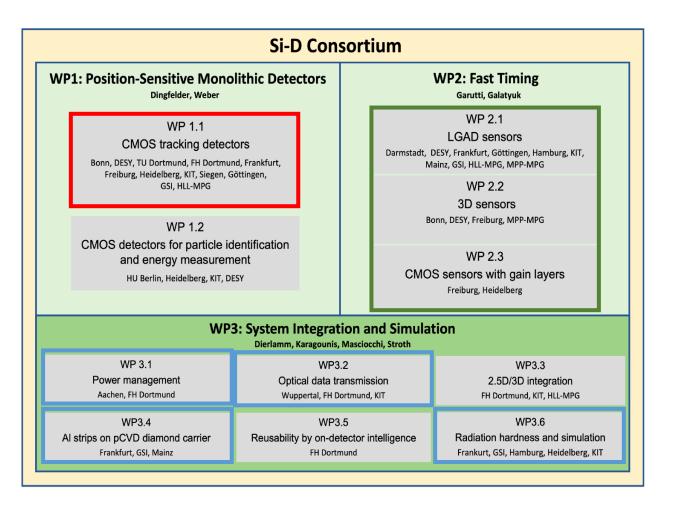
**DESY** 

GSI

**HLL-MPG** 

MPP-MPG

## (Partially) funded projects



WP1.1.1 Low-cost, large-area CMOS sensors with short strips (Freiburg, FH & TU Dortmund, Bonn, DESY)
WP 1.1.2 Monolithic sensors for vertex layers

WP 1.1.2 Monolithic sensors for vertex layers (Heidelberg, KIT)

WP 1.1.3 All-silicon modules (Bonn, TU Dortmund, Göttingen, Siegen, HLL)

WP2.1.1 Fast timing layer (DESY, Hamburg, Mainz, Göttingen)

WP2.1.2 A German LGAD for 4D tracking (Hamburg, HLL, MPP, KIT)

WP2.2 3D sensors for fast timing (sensor & R/O Chip) (Freiburg, Bonn, MPP, DESY)

WP2.3 CMOS sensor with gain layer (Freiburg, Heidelberg)

WP3.1 Power management

(Aachen, FH Dortmund)

WP3.2 Optical data transmission

(KIT, Wuppertal, FH Dortmund)

WP3.6 Radiation hardness/simulation

(Frankfurt, Hamburg, Heidelberg, KIT, GSI)

WP Al strips on pCVD carriers

(Frankfurt, Mainz, GSI)

## Cooperation agreement

zwischen der

Universität Heidelberg

Kooperationsvereinbarung - Projekt: R&D Detektoren: Siliziumdetektoren ("Silicon-D")

## Cooperation agreement almost finished

One last disagreement related to requests from U. Frankfurt and KIT (§10 "Einbindung von Dritten") still to be solved

Deadline for getting all signatures: Feb. 15, 2025

#### Kooperationsvereinbarung

```
Rheinischen Friedrich-Wilhelms-Universität Bonn
vertreten durch den Rektor, dieser vertreten durch den Kanzler,
Regina-Pacis-Weg 3, 53113 Bonn
       Ausführende Stelle:
                              Ausführende Stelle: Physikalisches Institut
                              (Prof. Dr. Jochen Dingfelder)
                                                                 - im Folgenden "Universität Bonn"
                                                                     oder "Koordinator" genannt -
und
RWTH Aachen University KdöR
vertreten durch den Rektor, Templergraben 55, 52062 Aachen
       Ausführende Stelle: Lehrstuhl für Experimentalphysik I B und I. Physikalisches Institut
                            (Prof. Dr. Lutz Feld)
                                                                - im Folgenden "RWTH" genannt -
Johann Wolfgang Goethe-Universität Frankfurt am Main
vertreten durch den Präsidenten, Theodor-W.-Adorno-Platz 1, 60323 Frankfurt am Main
       Ausführende Stelle: Institut für Kernphysik (Prof. Dr. Joachim Stroth)
                                                                 - im Folgenden "UFRA" genannt -
und
Albert-Ludwigs-Universität Freiburg
vertreten durch die Rektorin, Prof. Dr. Kerstin Kieglstein
Friedrichstr. 39, 79098 Freiburg im Breisgau
       Ausführende Stelle: Physikalisches Institut (Prof. Dr. Karl Jakobs)
                                                                   - im Folgenden "UFR" genannt -
Georg-August-Universität Göttingen/ Georg-August-Universität Göttingen Stiftung Öffentlichen
Rechts (Stiftungsuniversität Göttingen)
vertreten durch den Präsidenten, Wilhelmsplatz 1, 37073 Göttingen
       Ausführende Stelle: II. Physikalisches Institut, Prof. Dr. Arnulf Quadt
                                                                  - im Folgenden "UGÖ" genannt -
und
Universität Hamburg
vertreten durch den Präsidenten
       Ausführende Stelle: Institut für Experimentalphysik (Prof. Dr. Erika Garutti)
                                                                  im Folgenden "UHH" genannt –
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VID 30383 Seite 1 von 30

## Expressions of Interest for detector concepts for FCC

## **Next Steps: Submit EOIs**

#### **The Calls**

Deadline Jan 31 for submission of EOIs to PED (us)

- for editorial feedback and iteration
- and inclusion in combined FCC submission summary
  - we will write an executive summary or cover letter
    - to be circulated with all submitters
  - attach Eols in pdf format to common FCC submission
    - no template
- EOI submitters are free to chose
  - independent submission to ESU (we'd appreciate to remain posted)
  - being attached to FCC common submission (default, let us know otherwise)
  - both (let us know)

#### **Deadline Mar 31** for submission to **ESU**

- submission of executive summary and attached EoIs (optional)
- submission of EOIs (independent or in parallel)

#### Content, on 2-4 pages (3-6 for concepts):

- The scope of planned activities for the next 3-5 years
- The Partners (Institutes) and their expertise
- The names of one or two contact persons
- The connection with technological activities in the DRD framework
- The engineering and simulation connections with concept groups
- References to relevant more detailed documentation of the technologies

DESY. Detector Concepts | Felix Sefkow | January 2025

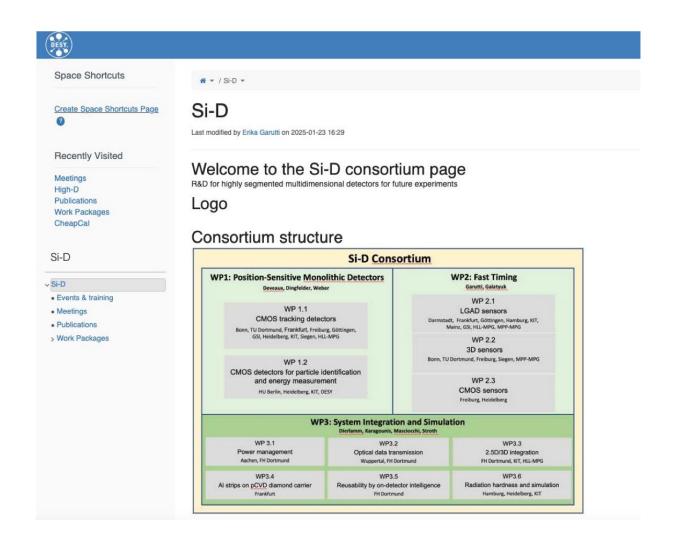
From Presentation by F. Sefkow at 8<sup>th</sup> FCC workshop at CERN (Jan. 18, 2025) https://indico.cern.ch/event/1439509/

- From discussions with colleagues, the plan (so far) is to submit two EOIs
  - Vertex detector → TPSCo 65 nm (OCTOPUS)
  - Main tracker → Large-area CMOS sensors
- Deadline for EOIs (~ 2 pages) very soon: January 31st
- If someone plans to submit an EOI or would like to join the EOIs above, please let us know

## Organizational issues

- Si-D web page (xWiki)
  - → see presentation from Erika

• Si-D logo?



## Si-D Meeting at Terascale Detector Workshop 2025



Helmholtz Alliance

## **PHYSICS AT THE TERASCALE**





#### **Organizing Committee**

Jochen Dingfelder, Doris Eckstein, Lutz Feld, Tobias Flick, Ulrich Husemann, Oliver Kortner, Lucia Masetti, Andreas Mussgiller, Ulrich Parzefall, Hans-Christian Schultz-Coulon, Felix Sefkow, Frank Simon, Arno Strässner

#### **Local Organizers**

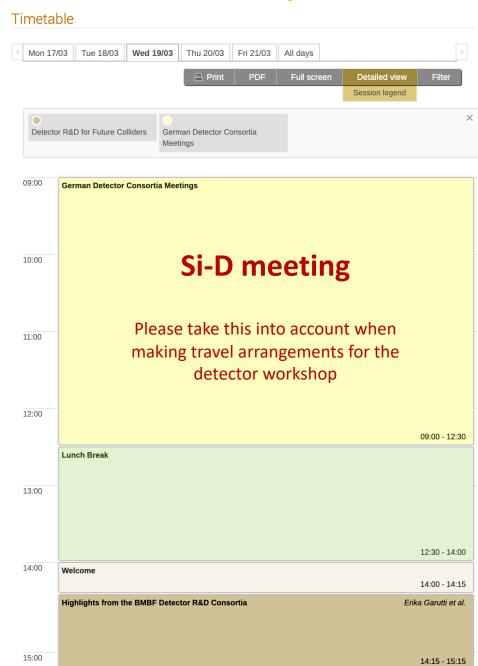
Markus Ball, Florian Bernlochner, Klaus Desch, Yannick Dieter, Jochen Dingfelder, Matthias Hamer, Philip Hauer, Fabian Hügging, Jochen Kaminski, Bernhard Ketzer, Sebastian Neubert. Matthias Schott, Slavomira Stefkova, Marco Vogt

#### Website:

https://indico.desy.de/event/47789/



Please register by March 3, 2025

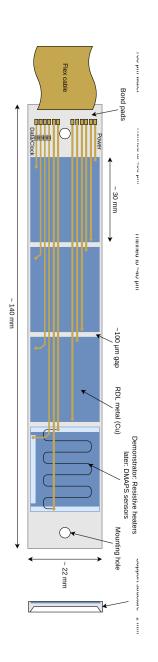


# Backup

## WP1: Position-sensitive monolithic detectors

## WP 1.1 CMOS tracking detectors

- CMOS strip detectors in 150 nm LFoundry technology (Freiburg, FH & TU Dortmund, Bonn, DESY)
  - Cost-effective large-area CMOS sensors (reticle stitching)
  - Design active strixel sensors: short strips, integrated FE electronics
- Monolithic sensor in 130 nm SiGe BiCMOS technology (Heidelberg, KIT)
  - $\circ$  High rate capability (HBT  $\rightarrow$  fast amplifiers/transmitters up to 10 Gbps)
- MAPS in 65nm TPSCo technology (Heidelberg, Frankfurt, GSI)
  - Sensor characterization & qualification of stitched sensors
    - → towards large-area & bent sensors
  - Simulations for optimization of pixel design and radiation hardness
- All-silicon modules for DMAPS (Bonn, TU Dortmund, Göttingen, Siegen, HLL)
  - Ultra-light module design
  - Integration of power and readout lines directly on wafer (RDL)



## WP1: Position-sensitive monolithic detectors

## WP 1.2 CMOS detectors for "non-tracking" applications

- Monolithic sensors with high dynamic range for PID (KIT, Heidelberg)
  - PID through dE/dx measurement in HVMAPS (large depleted region)
  - High-dynamic-range ADC in every pixel
  - Further design optimization to improved dynamic range
- DMAPS for digital calorimeters (HU Berlin, DESY)
  - DMAPS provide high granularity for counting tracks in shower
  - Investigation of new data reduction techniques (hit/cluster counting)
  - New sensor design with on-chip digital processing capabilities suitable for digital calorimeter readout

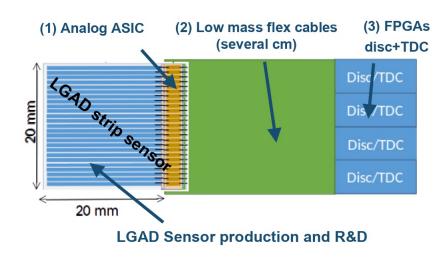


## WP2: Fast timing

### WP 2.1 LGADs

- Fast timing layer (DESY, Hamburg, Mainz, Göttingen)
  - Timepix4-based timing layer in EUDET telescope
  - Available to all groups for test-beam measurements of various LGAD layers
- German LGAD for 4D tracking (Hamburg, HLL, MPP, KIT)
  - Novel LGAD design by HLL (MARTHA)
  - Characterization of first prototypes developed for photon science
  - Goal: New optimized design for particle physics expts (timing, rad. hardness) + new readout ASIC (IHP 130nm BiCMOS)
- Large-area, low-mass 4D tracking demonstrator (TU Darmstadt, GSI, KIT)
  - Novel 4D tracking concept based on separation of FE electronics and sensor
  - Goal: Combine single modules to large-area system (100 cm²)

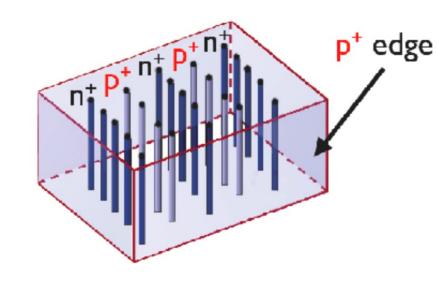




## WP2: Fast timing

### WP 2.2 3D sensors (Freiburg, Bonn, MPP, DESY)

- Novel radiation-hard 3D sensors dedicated to fast timing (based on cooperation within RD50 – CNM Barcelona, Ljubljana)
- Design of dedicated readout ASIC with high-bandwidth analog FE adapted to large sensor capacitance



## WP 2.3 CMOS sensors with gain layers (Freiburg, Heidelberg)

- Improve time resolution of CMOS sensors with gain layers (→ higher S/N)
- "Implementing LGADs in CMOS technology"

## WP3: System integration, radiation tolerance, and simulation

### WP 3.1 Power management (Aachen, FH Dortmund)

o DC-DC converters with larger conversion factors, new circuit designs to reduce power dissipation

### WP 3.2 Optical data transmission (KIT, Wuppertal, FH Dortmund)

Optical transmission based on chips integrating silicon-photonics components

## WP 3.3 2.5/3D integration (KIT, FH Dortmund, HLL-MPG)

- Integration of chips with active interposers (2.5D) or vertical stacking with TSVs (3D)
- Advanced wafer bonding techniques

## WP 3.4 Aluminium strip lines on pCVD diamond carriers (Frankfurt, Mainz, GSI)

o Combine mechanical support, cooling, electrical connectivity in one (low-material) component

## WP 3.5 Reusability by on-detector intelligence (FH Dortmund)

- Programmability/reconfigurability through radiation-hard, SEU-tolerant RISC-V CPUs & FPGAs
- On-detector chip intelligence, e.g. hardware accelerators for AI and ML

## WP 3.6 Radiation hardness and simulations (Frankfurt, Hamburg, Heidelberg, KIT, GSI)

